



宇腾科技
SYT TECH

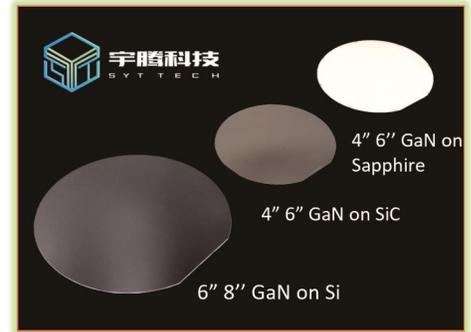
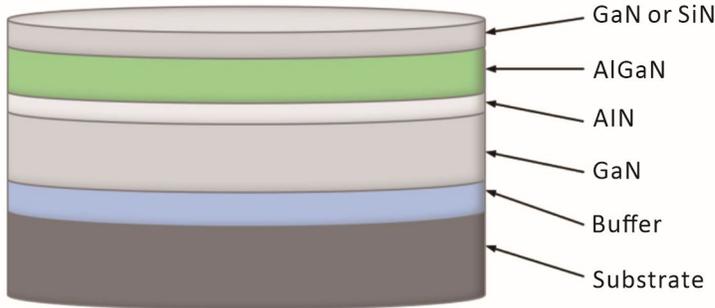
GaN Epi Wafer Material Properties

Shaanxi Yuteng Electronic Technology Co., Ltd.



Respect Quality Improve Efficiency
Timely Feedback Meet Challenges

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Hall

RESULTS SUMMARY

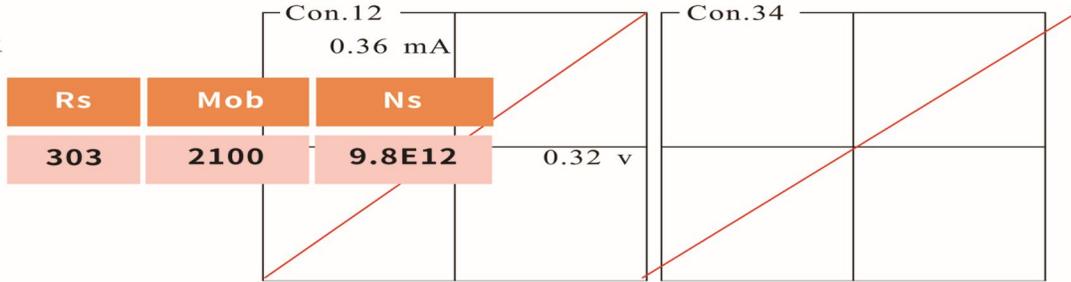
Rs: 303.3 ohm/sq
R : 0.06066 ohm-cm

Rhs: -63.6 M²C
Mob: 2.1e+03 cm²v⁻¹s⁻¹

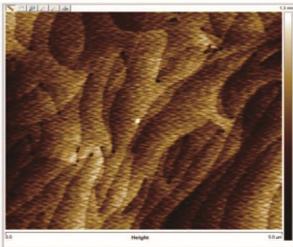
Na: -9.814e+12 /cm²
N : -4.907e+16 /cm³

CONTACT CHECK

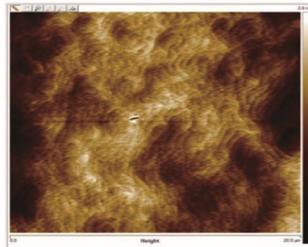
Pair	ohms
12	878
23	965
34	999
41	881
13	875
24	1130



AFM

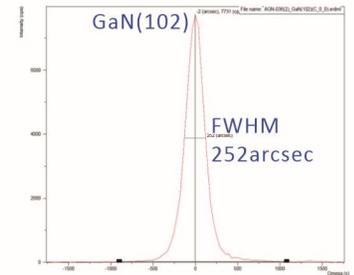
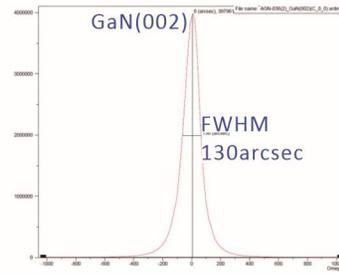


rms: 0.196 nm (5x5um²)

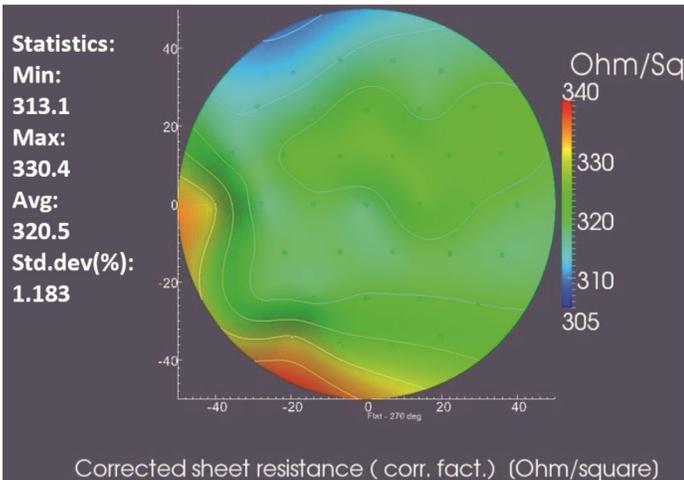


rms: 0.433 nm (20x20 um²)

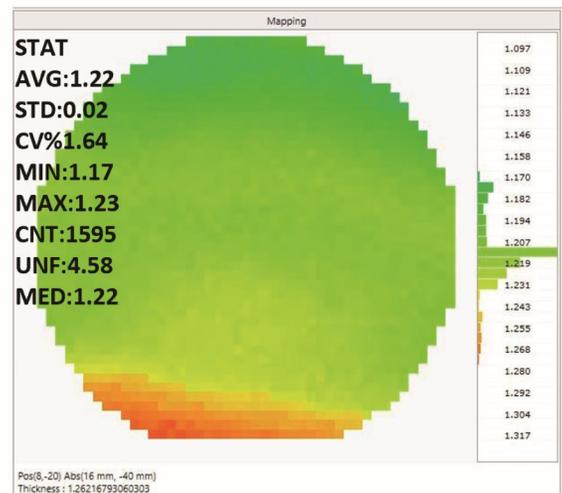
XRD Rocking curves



Rs distribution



GaN thickness mapping





GaN Epitaxial Wafer

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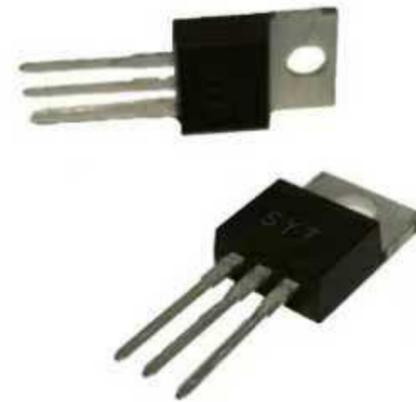
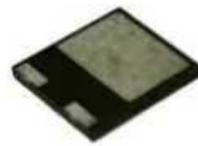
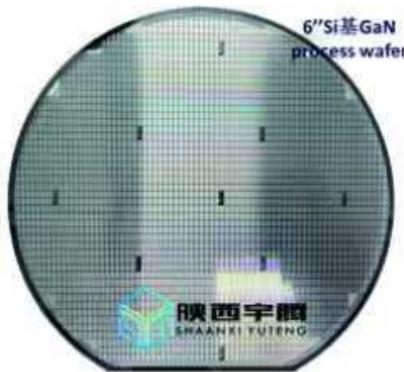
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GaN Epitaxial Wafer

Most suitable for RF device and power device applications with excellent performance.

The characteristics of GaN power devices: can reduce the energy loss in the process of switching and switching, and realize the efficient transmission and utilization of energy.

GaN devices are gradually replacing silicon-based products as key materials for electric motors, electric vehicles, smart grids and renewable energy.



SYT 650V GaN Device Type

Product Model	Package	Vds(V)	Id(A)	Rds(mΩ)	Vth(V)	Qg(nC)	Qrr(nC)
SYT065D009R2700	Bare Chip	650	9	270	-16	—	—
SYT065D013R2250	Bare Chip	650	13	225	-19	—	—
SYT065D018R1500	Bare Chip	650	18	150	-13	—	—
SYT065D045R0350	Bare Chip	650	45	35	—	—	—
SYT120D012R1500	Bare Chip	1200	12	150	—	—	—
SYT120D045R0350	Bare Chip	1200	45	35	—	—	—
SYT065D030R0500	Bare Chip	650	30	50	—	—	—
SYT065D030R050D	DFN 8*8	650	30	50	—	—	—
SYT065D030R050T	TO-247	650	30	50	—	—	—
SYT120D030R0500	Bare Chip	1200	30	50	—	—	—
SYT120D030R050D	DFN 8*8	1200	30	50	—	—	—
SYT120D030R050T	TO-247	1200	30	50	—	—	—
SYT065D009R240D	DFN 8*8	650	9	240	2	21	39
SYT065D009R240T	TO-252	650	9	240	2	21	39
SYT065D011R230D	DFN 8*8	650	11	230	1.8	12.5	38
SYT065D013R180T	TO-220	650	13	180	4	20	26
SYT065D014R180D	DFN 8*8	650	14	180	4	20	26
SYT065D018R120D	DFN 8*8	650	18	120	4	21	26
SYT065D023R120T	TO-220	650	23	120	4	21	26
SYT065D038R050T	TO-247	650	38	50	4	—	—
SYT070D015R125T	TO-220	700	15	125	4	—	—
SYT120D012R150D	DFN 8*8	1200	12	150	1.6	12.3	—
SYT120D025R080T	TO-247	1200	25	80	2.9	—	—
SYT120D030R050TA	TO-220	1200	30	50	1.6	—	—
SYT120D030R050TB	TO-220	1200	30	50	4	—	—

Shaanxi Yuteng Electronic Technology Co., Ltd. focuses on: 6", 8" silicon based gallium nitride epitaxy (GaN on Si). 4" and 6" gallium nitride (GaN on SiC) epitaxial on silicon carbide substrate. 4" and 6" gallium nitride (GaN) epitaxial on sapphire substrate. Yuteng Technology (SYT GaN™) HEMT structural products come in two types: medium and high voltage D-mode and E-mode. GaN processing chips and GaN device products that support power and RF applications can also be provided. Please discuss the specifications in detail.